

60V N-Channel Power MOSFET

TO-252 (DPAK)



Pin Definition:

- 1. Gate
- 2. Drain
- 3. Source

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)
60	7.3 @ V _{GS} =10V	66

Features

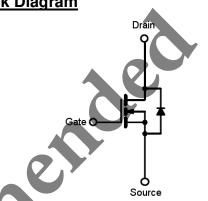
- Advanced Trench Technology
- Low $R_{DS(ON)}$ 7.3m Ω (Max.)
- Low gate charge typical @ 81nC (Typ.)
- Low Crss typical @ 339pF (Typ.)

Ordering Information

Part No.	Package	Packing		
TSM60N06CP ROG	TO-252	2.5Kpcs / 13" Reel		

Note: "G" denote for Halogen Free Product





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Absolute Maximum Rating (T_C = 25°C unless otherwise noted

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	60	V	
Gate-Source Voltage		V_{GS}	±20	V	
	T _C = 25°C		66	А	
Continuous Drain Current	$T_C = 70^{\circ}C$		53		
Continuous Diam Current	$T_A = 25^{\circ}C$	l _D	13		
	$T_A = 70^{\circ}C$		10		
Drain Current-Pulsed Note 1		I_{DM}	150	Α	
Avalanche Current, L = 0.1mH		I_{AS}, I_{AR}	53	Α	
Avalanche Energy, L = 0.1mH		E_{AS},E_{AR}	400	mJ	
	$T_C = 25^{\circ}C$		44.6		
Maximum Rower Distinction	$T_C = 70^{\circ}C$	В	28.6	W	
Maximum Power Dissipation	$T_A = 25^{\circ}C$	P_{D}	2		
>	$T_A = 70^{\circ}C$		1.3		
Storage Temperature Range		T_{STG}	-55 to +150	°C	
Operating Junction Temperature Range		T_J	-55 to +150	°C	

^{*} Limited by maximum junction temperature

Thermal Performance

Thormal Torrormanoo					
Parameter	Symbol	Limit	Unit		
Thermal Resistance - Junction to Case	R _{eJC}	2.8	°C/W		
Thermal Resistance - Junction to Ambient	R _{OJA}	62	°C/W		

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Electrical Specifications (T_C = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	60			٧
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 30A$	R _{DS(ON)}		6.3	7.3	mΩ
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	$V_{GS(TH)}$	2	3	4	V
Zero Gate Voltage Drain Current	$V_{DS} = 48V, V_{GS} = 0V$	I _{DSS}			1	uA
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
Dynamic						
Total Gate Charge	V 00V I 00A	Q_g		81	-	
Gate-Source Charge	$V_{DS} = 30V, I_{D} = 30A,$	Q_{gs}		23		nC
Gate-Drain Charge	$V_{GS} = 10V$	Q_{gd}		24		
Input Capacitance	V 00V V 0V	C _{iss}		4382		
Output Capacitance	$V_{DS} = 30V, V_{GS} = 0V,$	C _{oss}	-	668		pF
Reverse Transfer Capacitance	f = 1.0MHz	C _{rss}	7	339		
Switching						
Turn-On Delay Time		t _{d(on)}		25		
Turn-On Rise Time	$V_{GS} = 10V, V_{DS} = 30V,$	t _r		19		0
Turn-Off Delay Time	$R_G = 3.3\Omega, I_D = 30A$	$t_{d(off)}$		85		nS
Turn-Off Fall Time		t _f		43		
Drain-Source Diode Characteristics and Maximum Rating						
Drain-Source Diode Forward Voltage	$V_{GS} = 0V, I_S = 20A$	V _{SD}	-	0.8	1.3	>
Reverse Recovery Time	I _S ≠ 30A, T _J = 25 °C	t _{fr}		36		nS
Reverse Recovery Charge Notes:	dl/dt = 100A/us	Q _{fr}		53		nC

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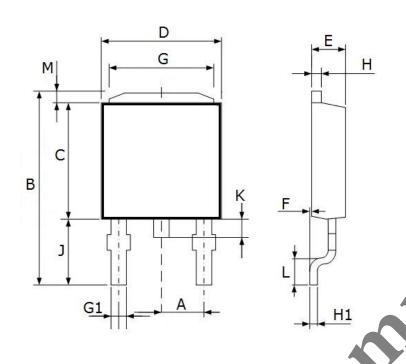
Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
 R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{θJC} is guaranteed by design while R_{θCA} is determined by the user's board design. R_{θJA} shown below for single device operation on FR-4 in still air







TO-252 Mechanical Drawing



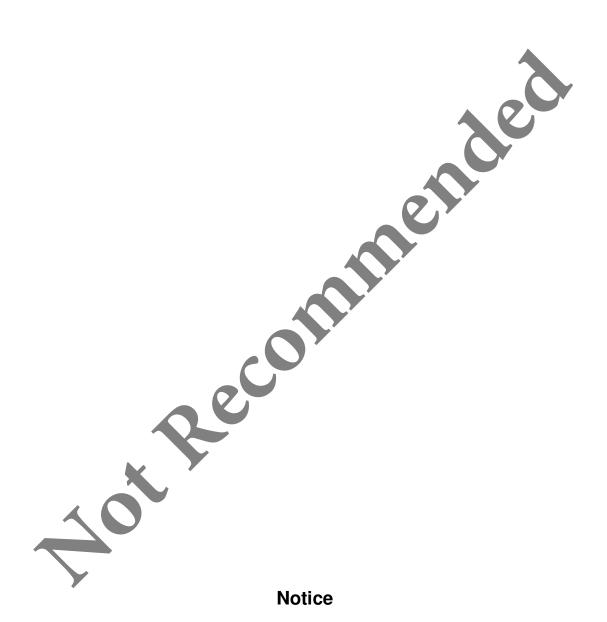
TO-252 DIMENSION						
DIM	MILLIM	ETERS	INCHES			
ווועו	MIN	MAX	MIN	MAX		
Α	2.286	BSC	0.090	0.090 BSC		
В	9.40	10.40	0.370	0.409		
С	5.40	6.23	0.213	0.245		
D	6.40	6.80	0.252	0.268		
Е	2.20	2.40	0.087	0.094		
F	0.00	0.20	0.000	0.008		
G	5.20	5.50	0.205	0.217		
G1	0.50	0.91	0.020	0.036		
Н	0.45	0.60	0.018	0.024		
H1	0.40	0.60	0.016	0.024		
	2.50	2.90	0.098	0.114		
K	0.60	1.00	0.023	0.039		
7	1.40	1.78	0.055	0.070		
М	0.88	1.28	0.034	0.050		

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